

**Amendment and Response under 37 C.F.R. 1.116**

Applicant: Thomas C. Anthony

Serial No.: 10/612,676

Filed: July 2, 2003

Docket No.: 10014296-1

Title: MAGNETIC MEMORY DEVICE

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**REMARKS**

The following remarks are made in response to the Final Office Action mailed April 25, 2005, in which claims 1-12 and 29-32 were rejected. With this Response, claims 1, 29 and 30 are amended. Claims 1-12 and 29-32 remain pending in the application and are presented for reconsideration and allowance.

**Claim Rejections under 35 U.S.C. § 102**

Claims 1-3 and 8 and 9 stand rejected under 35 U.S.C. §102(e) as being anticipated by Childress et al. (U.S. Patent Application Publication No. 2003/0231437).

Regarding claim 1, the Examiner asserts Childress et al. discloses a memory wafer comprising a first surface (of substrate 9, 109 in Figures 1 and 2) having memory chips disposed thereon, the memory chips defining an exterior face (150 of Figure 2) of the memory wafer. The Examiner notes that the magnetic tunnel junction (MTJ) of Childress is used in nonvolatile memory elements or cells for MRAM, and that substrate 9 (Fig. 1) would be a silicon wafer if the device is a memory cell). The Examiner further alleges Childress et al. discloses a second surface (of substrate 9, 109) opposite the exterior face 150, and a top magnetically permeable shield layer (made of permalloy as the permeable shield layer) on top surface 150 (not shown).

As amended, independent claim 1 claims a memory wafer comprising: a first surface having a plurality of unseparated memory chips disposed thereon, the memory chips defining an exterior face of the memory wafer; a second surface opposite the exterior face; and a magnetically permeable shield layer extending over the entirety of at least one of the exterior face and the second surface of the memory wafer. The memory wafer as set forth in amended claim 1 is shown, for example, in Figure 1 of the application.

Under 35 U.S.C. §102, **the cited reference must show each and every feature of the claimed invention.** Extension of or speculation as to the cited teaching is permitted only when *necessarily present* in the disclosed apparatus or method. In other words, if a particular feature is not specifically disclosed it can only be relied upon under 35 U.S.C. §102 if and only if such feature is necessarily present in the disclosed apparatus or method. See, *Verdegaal Bros. v. Union Oil Co. of California*, 814 F.2d 628, 631, 2 USPQ2d 1051, 1053

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(Fed. Cir. 1987)( “A claim is anticipated only if each and every element as set forth in the claim is found, either expressly or inherently described, in a single prior art reference”), and *Richardson v. Suzuki Motor Co.*, 868 F.2d 1226, 1236, 9 USPQ2d 1913, 1920 (Fed. Cir. 1989) (“The identical invention must be shown in as complete detail as is contained in the ... claim”).

The specification of the present application clearly describes, in paragraphs 25 and 26, that a memory wafer 100 includes a plurality of memory chips 110, each of the memory chips 110 include multiple memory arrays 120, and each of the memory arrays have multiple memory cells 126. As shown in Figure 1 of the application, the plurality of memory chips 110 disposed on the first surface are in an unseparated condition, and shield layer 180 extends over the entirety of the bottom surface of the wafer 100. Childress et al. fails to anticipate the subject matter of amended claim 1 for at least the reason that Childress et al. fails to disclose or suggest a memory wafer having a **plurality of unseparated** memory chips disposed thereon. Rather, Childress et al. discloses a **single** magneto-resistive element on a substrate, and the single magneto-resistive element is shown as a separated element. The disclosure of Childress et al. relates to a **single** magneto-resistive element in isolation, and does not show, teach or suggest a first surface of a wafer having a **plurality of unseparated memory chips** disposed thereon. Clearly, the single magneto-resistive element disclosed by Childress et al., cannot be said to be the same as the memory chips and memory wafer in claim 1. The single magneto-resistive element of Childress et al. is distinctly different from a memory wafer having a plurality of unseparated memory chips disposed thereon, and a plurality of memory chips are *not necessarily present* in the reference. The position that a plurality of magneto-resistive devices are not necessarily present in Childress et al., is supported by the fact that the read head of Childress et al. only requires a single magneto-resistive device.

Amended claim 1 further sets forth that the memory wafer includes “a magnetically permeable shield layer extending over the entirety of at least one of the exterior face and second surface of the memory wafer.” As described above, Childress et al. does not disclose a memory wafer having memory chips disposed thereon. Rather, Childress et al. discloses a single magneto-resistive cell. The shield layer mentioned in Childress et al. is discussed only with respect to the single isolated magneto-resistive cell and, accordingly, Childress et al.

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does not *necessarily* disclose a magnetically permeable shield layer **extending over the entirety of a surface of a memory wafer.**

For at least the reasons provided above, the claimed memory wafer is not anticipated by Childress et al., and the claimed elements are not *necessarily present* in the reference. Accordingly, claim 1 is in allowable condition, and withdrawal of the rejection of claim 1 under 35 U.S.C. §102(e) is respectfully requested.

Claims 2, 3, 8 and 9 depend, either directly or indirectly, from amended independent claim 1 which is in allowable condition for at least the reasons set forth above. Accordingly, dependent claims 2, 3, 8 and 9 are also in allowable condition, and withdrawal of the rejection under 35 U.S.C. §102(e) is respectfully requested.

**Claim Rejections under 35 U.S.C. § 103**

Claims 4-7 and 10-12 stand rejected under 35 U.S.C. §103(a) as being unpatentable over Childress et al. (U.S. Patent Application Publication No. 2003/0231437) in view of Rizzo et al. (U.S. Patent Application Publication No. 2004/0000415).

Claims 4-7 and 10-12 each depend, either directly or indirectly, from amended independent claim 1 which is in allowable condition for at least the reasons set forth above. As described above, Childress et al. fails to anticipate or suggest the elements of independent claim 1. Rizzo et al. does not remedy the deficiencies of Childress et al., as Rizzo et al. also fails to disclose or suggest a memory wafer having a plurality of unseparated memory chips disposed thereon, and further fails to disclose or suggest a magnetically permeable shield layer extending over the entirety of at least one of the exterior face and the second surface of a memory wafer. In fact, as best seen in Figures 1-7, Rizzo et al. teaches away from the claimed invention by teaching a magnetic material layer 30 that extends over **less** than the entirety of the substrate 10. Accordingly, the combination of Childress et al. and Rizzo et al. also fails to teach or suggest the elements of the claims depending from amended independent claim 1. For at least these reasons, dependent claims 4-7 and 10-12 are not obvious over Childress et al. in view of Rizzo et al. Accordingly, withdrawal of the rejection of claims 4-7 and 10-12 under 35 U.S.C. §103(a) is respectfully requested.

Claims 29 and 30 stand rejected under 35 U.S.C. §103(a) as being unpatentable over

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Childress et al. (U.S. Patent Application Publication No. 2003/0231437) in view of Tuttle et al. (U.S. Patent Application Publication No. 2003/01322494).

Regarding claim 29, Childress et al. is alleged to disclose a memory wafer comprising a first surface (of substrate 9, 109 in Figures 1 and 2) having memory chips disposed thereon, the memory chips defining an exterior face 150 of the memory wafer. The Examiner notes that the magnetic tunnel junction (MTJ) of Childress is used in nonvolatile memory elements or cells for MRAM, and that substrate 9 (Fig. 1) would be a silicon wafer if the device is a memory cell. Childress et al. is further alleged to disclose a second surface (of substrate 9, 109) opposite the exterior face 150, and a top magnetically permeable shield layer on top of surface 150 (not shown). Childress et al. is acknowledged as failing to explicitly show means for protecting the memory cells from stray magnetic fields. However, Tuttle et al. is cited as showing the use of magnetically permeable foils 26 and 28 as shields from stray magnetic fields. The Examiner alleges the magnetically permeable layers of the Childress et al. device are identical to the shields of Tuttle et al., and therefore alleges that the magnetically permeable layers of Childress et al. can be used as means for protecting from external magnetic fields.

Amended independent claim 29, similar to claim 1 discussed above, is directed to a memory wafer including a first surface having a plurality of unseparated memory chips disposed thereon, and means for protecting the memory chips from stray magnetic fields extending over the entirety of at least one of the exterior face and the second surface of the memory wafer. As discussed above with respect to independent claim 1, Childress et al. discloses only a single memory cell. Childress et al. fails to disclose an array of memory cells or a memory chip comprised of a plurality of memory cell arrays, much less a memory wafer having a plurality of unseparated memory chips as described and claimed in the present application. Further, Childress et al. does not disclose or suggest means for protecting the memory chips from stray magnetic fields extending over the entirety of at least one of the exterior face and the second surface of the memory wafer. For at least the reasons set forth above, the claimed elements are not *necessarily present* in Childress et al.

Tuttle et al. fails to remedy the deficiencies of Childress et al., as Tuttle et al. also fails to disclose or suggest a memory wafer having a plurality of unseparated memory chips disposed thereon. Rather, Tuttle et al. discloses package 10 for an individual integrated

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circuit. Tuttle et al. also fails to disclose or suggest means for protecting the memory chips from stray magnetic fields extending over the entirety of at least one of the exterior face and the second surface of the memory wafer. Rather, Tuttle et al. teaches attaching a foil of magnetic material to a package after the separated integrated circuit 12 is encapsulated within a molded body 14. (See Tuttle et al., para. [0028] stating “magnetically permeable foils 26, 28 are attached to both the top and bottom outer surfaces of the molded body 14.”)

Accordingly, the subject matter of independent claim 29 is not obvious in view of the combination of Childress et al. and Tuttle et al. for at least these reasons. Accordingly, withdrawal of the rejection of amended independent claim 29 under 35 U.S.C. §103(a) is respectfully requested.

Dependent claim 30 depends directly from independent claim 29, which is allowable for at least the reason set forth above. Claim 30 has been amended to conform to the language of independent claim 29, and specifically to change “memory cells” to --memory chips--. Because claim 30 depends from allowable claim 29, claim 30 is also in allowable condition, and withdrawal of the rejection of dependent claim 30 under 35 U.S.C. §103(a) is respectfully requested.

Claims 31 and 32 stand rejected under 35 U.S.C. §103(a) as being unpatentable over Childress et al. (U.S. Patent Application Publication No. 2003/0231437) in view of Tuttle et al. (U.S. Patent Application Publication No. 2003/01322494) and further in view of Rizzo et al. (U.S. Patent Application Publication No. 2004/0000415).

Dependent claims 31 and 32 depend from independent claim 29, which is in allowable condition for at least the reasons discussed above. Rizzo et al. fails to overcome the deficiencies of Childress et al. and Tuttle et al. As discussed above, Rizzo et al. fails to disclose a memory wafer having a plurality of unseparated memory chips disposed thereon. As also discussed above, Rizzo et al. teaches away from the claimed invention by teaching a magnetic material layer 30 that extends over less than the entirety of the substrate 10. According, dependent claims 31 and 32 are also in allowable condition, and withdrawal of the under 35 U.S.C. §103(a) is respectfully requested.

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**CONCLUSION**

For at least the reasons discussed above, claims 1-12 and 29-32 are in allowable condition and notice to that effect is respectfully requested.

The Examiner is invited to contact the Applicant's representative at the below-listed telephone numbers to facilitate prosecution of this application.

Any inquiry regarding this Amendment and Response should be directed to either Matthew B. McNutt at Telephone No. (512) 231-0531, Facsimile No. (512) 231-0540, or Phil Lyren at Telephone No. (281) 514-8236, Facsimile No. (281) 514-8332. In addition, all correspondence should continue to be directed to the following address:

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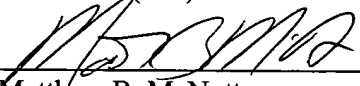
Respectfully submitted,

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**CERTIFICATE UNDER 37 C.F.R. 1.8:** The undersigned hereby certifies that this paper or papers, as described herein, are being deposited in the United States Postal Service, as first class mail, in an envelope address to: Mail Stop AF, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on this 3<sup>rd</sup> day of June, 2005.

By   
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